





## BZT52C2V4 - BZT52C43 ZENER DIODES



#### **Features**

- Planar Die Construction
- 350mW Power Dissipation on Ceramic PCB
- General Purpose, Medium Current
- Ideally Suited for Automated Assembly Processes
- Available in Lead Free Version
- "-A" suffix is for Automotive qualified
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

## **Circuit Diagram**



#### **Mechanical Data**

- Case: SOD-123, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202,

Method 208

Polarity: Cathode BandWeight: 0.01 grams(approx)

### Maximum Ratings @T<sub>A</sub>=25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Forward Voltage (Note 2) @I <sub>F</sub> =10mA	V <sub>F</sub>	0.9	V
Power Dissipation(Note 1)	P <sub>D</sub>	350	mW
Thermal resistance junction to Ambient	R <sub>θJA</sub>	357	°C/W
Junction Temperature	TJ	150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C







# Electrical Characteristics @T<sub>A</sub>=25°C unless otherwise specified

Type Number	Type Code	Zener Voltage Range (Note 2)			Maximum Zener Impedance (Note 3)		Maximum Reverse Current (Note 2)		Typical Temperature Coefficent		Test Current		
			V <sub>Z</sub> @I <sub>ZT</sub>		I <sub>ZT</sub>	Z <sub>ZT</sub> @I <sub>ZT</sub>	Z <sub>ZK</sub> @I <sub>ZK</sub>	I <sub>ZK</sub>	I <sub>R</sub>	V <sub>R</sub>	mV	// anno	
	2000000	Nom(V)	Min(V)	Max(V)	mA -		Ω	mA	uA	V	Min	Max	mA -
BZT52C2V4	WX	2.4	2.20	2.60	5	100	600	1.0	50	1.0	-3.5	0	5
BZT52C2V7	W1	2.7	2.5	2.9	5	100	600	1.0	20	1.0	-3.5	0	5
BZT52C3V0	W2	3.0	2.8	3.2	5	95	600	1.0	10	1.0	-3.5	0	5
BZT52C3V3	W3	3.3	3.1	3.5	5	95	600	1.0	5	1.0	-3.5	0	5
BZT52C3V6	W4	3.6	3.4	3.8	5	90	600	1.0	5	1.0	-3.5	0	5
BZT52C3V9	W5	3.9	3.7	4.1	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52C4V3	W6	4.3	4.0	4.6	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52C4V7	W7	4.7	4.4	5.0	5	80	500	1.0	3	2.0	-3.5	0.2	5
BZT52C5V1	W8	5.1	4.8	5.4	5	60	480	1.0	2	2.0	-2.7	1.2	5
BZT52C5V6	W9	5.6	5.2	6.0	5	40	400	1.0	1	2.0	-2.0	2.5	5
BZT52C6V2	WA	6.2	5.8	6.6	5	10	150	1.0	3	4.0	0.4	3.7	5
BZT52C6V8	WB	6.8	6.4	7.2	5	15	80	1.0	2	4.0	1.2	4.5	5
BZT52C7V5	wc	7.5	7.0	7.9	5	15	80	1.0	1	5.0	2.5	5.3	5
BZT52C8V2	WD	8.2	7.7	8.7	5	15	80	1.0	0.7	5.0	3.2	6.2	5
BZT52C9V1	WE	9.1	8.5	9.6	5	15	100	1.0	0.5	6.0	3.8	7.0	5
BZT52C10	WF	10	9.4	10.6	5	20	150	1.0	0.2	7.0	4.5	8.0	5
BZT52C11	WG	11	10.4	11.6	5	20	150	1.0	0.1	8.0	5.4	9.0	5
BZT52C12	WH	12	11.4	12.7	5	25	150	1.0	0.1	8.0	6.0	10.0	5
BZT52C13	WI	13	12.4	14.1	5	30	170	1.0	0.1	8.0	7.0	11.0	5
BZT52C15	WJ	15	13.8	15.6	5	30	200	1.0	0.1	10.5	9.2	13.0	5
BZT52C16	WK	16	15.3	17.1	5	40	200	1.0	0.1	11.2	10.4	14.0	5
BZT52C18	WL	18	16.8	19.1	5	45	225	1.0	0.1	12.6	12.4	16.0	5
BZT52C20	WM	20	18.8	21.2	5	55	225	1.0	0.1	14.0	14.4	18.0	5
BZT52C22	WN	22	20.8	23.3	5	55	250	1.0	0.1	15.4	16.4	20.0	5
BZT52C24	wo	24	22.8	25.6	5	70	250	1.0	0.1	16.8	18.4	22.0	5
BZT52C27	WP	27	25.1	28.9	2	80	300	0.5	0.1	18.9	21.4	25.3	2
BZT52C30	WQ	30	28.0	32.0	2	80	300	0.5	0.1	21.0	24.4	29.4	2
BZT52C33	WR	33	31.0	35.0	2	80	325	0.5	0.1	23.1	27.4	33.4	2
BZT52C36	ws	36	34.0	38.0	2	90	350	0.5	0.1	25.2	30.4	37.4	2
BZT52C39	WT	39	37.0	41.0	2	130	350	0.5	0.1	27.3	33.4	41.2	2
BZT52C39	WU	43	40.0	46.0	5	100	700	1.0	0.1	32	10.0	12.0	5

Notes: 1. Device mounted on ceramic PCB:  $7.6 mm\ x\ 9.4 mm\ x\ 0.87 mm\ with pad areas\ 25 mm^2$ 

2. Short duration test pulse used to minimize self-heating effect 3. f = 1 kHz

<sup>•</sup> China - Germany - Korea - Singapore - United States •

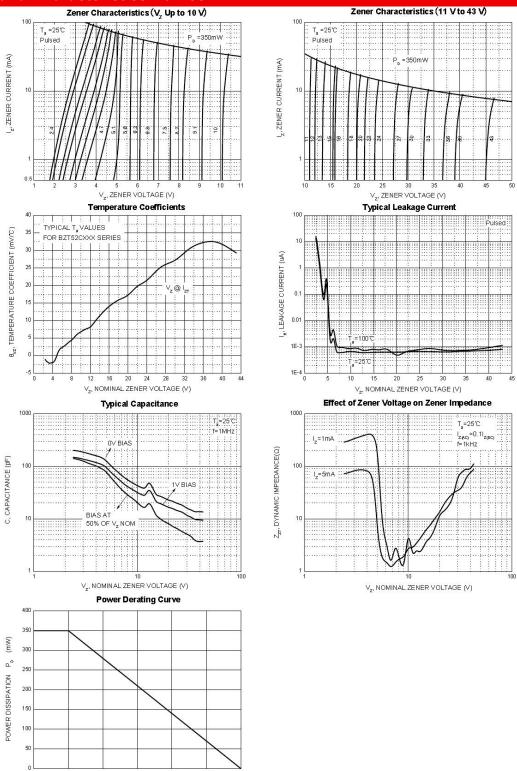
<sup>•</sup> http://www.smc-diodes.com - sales@ smc-diodes.com •







# **Ratings and Characteristics Curves**



• China - Germany - Korea - Singapore - United States •

AMBIENT TEMPERATURE  $T_a$  (°C)

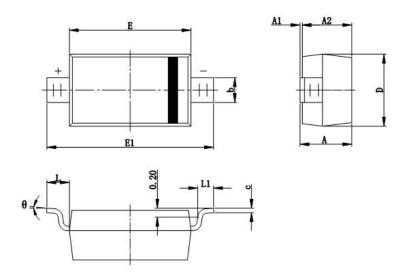
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## **Mechanical Dimensions SOD-123**



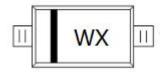
0)44501	Millin	neters	Inches			
SYMBOL	MIN.	MAX.	MIN.	MAX.		
Α	1.050	1.250	0.041	0.049		
A1	0.000	0.100	0.000	0.004		
A2	1.050	1.150	0.041	0.045		
b	0.450	0.650	0.018	0.026		
С	0.080	0.150	0.003	0.006		
D	1.500	1.700	0.059	0.067		
Е	2.600	2.800	0.102	0.110		
E1	3.550	3.850	0.140	0.152		
L	0.500	REF.	0.020 REF.			
L1	0.250	0.450	0.010	0.018		
θ	0°	8°	0°	8°		

## **Ordering Information**

Device	Package	Shipping		
BZT52C2V4 -	SOD-123	2000/		
BZT52C43	(Pb-Free)	3000pcs / reel		

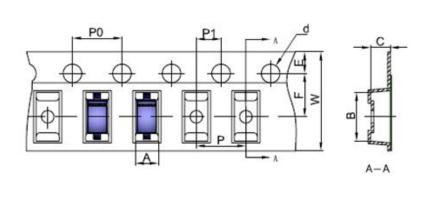
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

## **Marking Diagram**



WX = Type code

# **Carrier Tape Specification SOD-123**



SYMBOL	Millimeters				
STIMBOL	Min.	Max.			
Α	1.80	1.90			
В	3.89	3.99			
С	1.52	1.62			
d	1.45	1.65			
E	1.65	1.85			
F	3.40	3.60			
Р	3.90	4.10			
P0	3.90	4.10			
P1	1.90	2.10			
W	7.90	8.30			

- China Germany Korea Singapore United States
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#### BZT52C2V4 - BZT52C43



#### Technical Data Data Sheet N1966, Rev. A





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